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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
10/685,219	10/14/2003	Yaw S. Obeng	SILO-0016	4073
27964	7590 01/27/2006		EXAMINER	
HITT GAINES P.C. P.O. BOX 832570			UMEZ ERONINI, LYNETTE T	
RICHARDSON, TX 75083			ART UNIT	PAPER NUMBER
	•		1765	

DATE MAILED: 01/27/2006

Please find below and/or attached an Office communication concerning this application or proceeding.

				l				
		Application No.	Applicant(s)	_				
Office Action Summer		10/685,219	OBENG, YAW S.					
	Office Action Summary	Examiner	Art Unit	_				
		Lynette T. Umez-Eronini	1765					
Pe	The MAILING DATE of this communication apperiod for Reply	ears on the cover sheet with the o	correspondence address					
	A SHORTENED STATUTORY PERIOD FOR REPLY WHICHEVER IS LONGER, FROM THE MAILING DA - Extensions of time may be available under the provisions of 37 CFR 1.13 after SIX (6) MONTHS from the mailing date of this communication. If NO period for reply is specified above, the maximum statutory period w - Failure to reply within the set or extended period for reply will, by statute, Any reply received by the Office later than three months after the mailing earned patent term adjustment. See 37 CFR 1.704(b).	ATE OF THIS COMMUNICATION 36(a). In no event, however, may a reply be tinuity rill apply and will expire SIX (6) MONTHS from cause the application to become ABANDONE	N. nely filed the mailing date of this communication. ED (35 U.S.C. § 133).					
St	atus							
	1) Responsive to communication(s) filed on 14 O	<u>ctober 2003</u> .						
	· <u> </u>	, 						
	Since this application is in condition for allowance except for formal matters, prosecution as to the merits is							
	closed in accordance with the practice under E	x parte Quayle, 1935 C.D. 11, 4	53 O.G. 213.					
Di	sposition of Claims							
	4) ☐ Claim(s) 1-11 is/are pending in the application. 4a) Of the above claim(s) is/are withdraw 5) ☐ Claim(s) is/are allowed. 6) ☐ Claim(s) 1-11 is/are rejected. 7) ☐ Claim(s) is/are objected to. 8) ☐ Claim(s) are subject to restriction and/or	vn from consideration.						
Ą	oplication Papers							
	9) ☐ The specification is objected to by the Examine 10) ☑ The drawing(s) filed on 14 October 2003 is/are: Applicant may not request that any objection to the Replacement drawing sheet(s) including the correct 11) ☐ The oath or declaration is objected to by the Ex	a)⊠ accepted or b)⊡ objected drawing(s) be held in abeyance. Section is required if the drawing(s) is obj	e 37 CFR 1.85(a). jected to. See 37 CFR 1.121(d).					
Pr	iority under 35 U.S.C. § 119		•					
	12) Acknowledgment is made of a claim for foreign a) All b) Some * c) None of: 1. Certified copies of the priority documents 2. Certified copies of the priority documents 3. Copies of the certified copies of the prior application from the International Bureau * See the attached detailed Office action for a list of	s have been received. s have been received in Applicati ity documents have been receive (PCT Rule 17.2(a)).	on No ed in this National Stage					
٩tt	achment(s)							
- 1	Notice of References Cited (PTO-892)	4) Interview Summary						
.,	Notice of Draftsperson's Patent Drawing Review (PTO-948) Information Disclosure Statement(s) (PTO-1449 or PTO/SB/08) Paper No(s)/Mail Date 10/14/03 & 2/6/04.	Paper No(s)/Mail Date of Informal P 6) Other:	ate Patent Application (PTO-152)					

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DETAILED ACTION

Election/Restrictions

1. Applicant's election without traverse of claims 1-11 in the reply filed on 11/17/2005 is acknowledged.

Claim Rejections - 35 USC § 103

- 2. The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:
 - (a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.
- 3. This application currently names joint inventors. In considering patentability of the claims under 35 U.S.C. 103(a), the examiner presumes that the subject matter of the various claims was commonly owned at the time any inventions covered therein were made absent any evidence to the contrary. Applicant is advised of the obligation under 37 CFR 1.56 to point out the inventor and invention dates of each claim that was not commonly owned at the time a later invention was made in order for the examiner to consider the applicability of 35 U.S.C. 103(c) and potential 35 U.S.C. 102(e), (f) or (g) prior art under 35 U.S.C. 103(a).
- 4. Claims 1-6 and 8-11 are rejected under 35 U.S.C. 103(a) as being unpatentable over Sinha et al. (US 6,602,117 B1) in view of Prigge et al. (US 4,968,381).

As to claims 1-3 and 8-11, Sinha discloses a slurry for polishing a copper conductive structure of semiconductor device (Abstract). The slurry comprises at least one oxidizer, inhibitor and one or more abrasives (column 3, lines 11-13). Examples of the oxidizer includes potassium iodate (column 5, lines 34-40); corrosion inhibitors include benzotriazole, potassium silicate, and mixtures thereof and make up 0.05 % to 2 % by weight of the slurry (column 5, lines 52-66); and abrasive agents include alumina and silicon dioxide (SiO₂), (same as silica), (column 6, lines 1-3). The slurry can have a pH in the range of 3 to 7 and includes one or more pH control agents or buffers to adjust the pH to a desired level (column 6, lines 6-10). The aforementioned reads on,

A slurry for chemical mechanical polishing (CMP) a metal surface of a semiconductor substrate with a polyurethane free thermoplastic foam polishing body, comprising, an acid buffer that maintains said slurry at a pH between about 2.5 and about 4.0 during polishing of a metal surface on a semiconductor substrate.

Sinha differs in failing to teach an abrasive particle stabilizer, in claim 1;

wherein said abrasive particle stabilizer comprises molecules that are equivalent to repeating units of polymers comprising abrasive particles in said slurry, **in claim 4**;

wherein said abrasive particles comprise colloidal silica particles and said abrasive particle stabilizer comprises silicic acid and silicic salt, in claim 5; and

wherein a ratio of said silicic acid to said silicic salt is between about 100:1 and 1:100, in claim 6.

Prigge discloses a polishing solution that contains an additional polishing component containing 1 to 20% by volume of silicic acid or silicates (column 2, lines 5-

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11) and 1% by volume. The addition of silicic acid to a polishing solution resulted in haze-free polishing of a semiconductor wafer (column 6, lines 23-26).

Since the combination of Sinha's polishing composition comprising silicic acid and Prigge's polishing slurry comprising silica and a silicate salt is known, then the said combination would result in producing applicants' abrasive particle stabilizer. Hence, it would have been obvious to one having ordinary skill in the art at the time the invention was made to combine Prigge's slurry that contains silica and a silicate salt with Sinha's polishing slurry that contains silicic acid for the purpose of obtaining a haze-free wafer (see Prigge, column 6, lines 23-26).

5. Claim 7 is rejected under 35 U.S.C. 103(a) as being unpatentable over Sinha (US '117 B1) in view of Prigge (US '381) as applied to claim 1 above, and further in view of Sato (USA 5,906, 949).

Sinha in view of Prigge differs in failing to teach wherein said abrasive particle stabilizer comprises aluminate salts.

Sato discloses adding sodium aluminate (same as applicant's aluminate salt) to a slurry containing abrasive particles made of boehmite (same as applicant's alumina).

Since Sato illustrates the combination of abrasive particles comprising alumina and aluminate salt is known, then it would have been obvious to one having ordinary skill in the art at the time the invention was made to combine the slurries of Sinha and Prigge with a slurry comprising an aluminate salt as taught by Sato for the purpose of improving of the polishing rate without degradation in planarity of the processed surface and in the level of metal impurities (Sato, Abstract).

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Any inquiry concerning this communication or earlier communications from the examiner should be directed to Lynette T. Umez-Eronini whose telephone number is

571-272-1470. The examiner is normally unavailable on the First Friday.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Nadine Norton can be reached on 571-272-1465. The fax phone number for the organization where this application or proceeding is assigned is 571-273-8300.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

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Itue

January 17, 2006

NADINE G. NORTON SUPERVISORY PATENT EXAMPLER